

Layer-by-layer entangled spin-orbital texture of the topological surface state in Bi_2Se_3

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With their spin-helical metallic surface state, topological insulators (TIs) define a new class of materials with strong application potential in spintronics. Technological exploitation depends on the degree of spin polarization of the topological surface state (TSS), assumed to be 100% in phenomenological models. Yet in Bi_2Se_3 , an archetypical TI material, spin- and angle-resolved photoemission spectroscopy (S-ARPES) detects a spin polarization ranging from 20 to 85%, a striking discrepancy which undermines the applicability of real TIs. Here we show – studying Bi_2Se_3 by polarization-dependent ARPES and density-functional theory slab calculations – that the TSS Dirac fermions are characterized by a layer-dependent entangled spin-orbital texture, which becomes apparent through quantum interference effects. This explicitly solves the puzzle of the TSS spin polarization in S-ARPES, and suggests how 100% spin polarization of photoelectrons and photocurrents can be achieved and manipulated in TI devices by using linearly polarized light.

Topological insulators (TIs) define a new state of matter in which strong spin-orbit interaction (SOI) leads to the emergence of a metallic topological surface state (TSS) formed by spin-nondegenerate Dirac fermions [1–6]. To capture the physics of TIs, a spin-momentum locking with 100% spin polarization is usually assumed for the TSS in time-reversal invariant models [3–5]. A fully spin-polarized TSS has tantalizing properties, such as robust edge modes and exotic quasiparticle excitations, making TIs good candidates for spintronic applications [7]; and also a playground for engineering Majorana fermions, and exploiting their non-Abelian statistics in topological quantum computation [8]. The successful realization of topological insulating behavior in quantum wells [9, 10] and crystalline materials [11–13] brings us closer to the practical implementation of theoretical concepts built upon novel topological properties.

To this end, the fundamental question is that of the effective spin-polarization of the TSS Dirac fermions in real materials and devices, i.e. how realistic is the hypothesis of a 100% spin polarization. The large discrepancy in the degree of TSS spin polarization determined for Bi_2Se_3 by spin-resolved ARPES (angle-resolved photoemission spectroscopy) – ranging from 20 to 85% [14–18] – highlights the complexity of real TIs. First principle density-functional theory (DFT) calculations indicate that the TSS spin polarization in members of the Bi_2X_3 material family (X=Se, Te) can be substantially reduced from 100% [19, 20]. In addition, based on general symmetry arguments, it was shown that the spin polarization direction of photoelectrons in spin-resolved ARPES can be very different from that of the TSS wavefunction [21]. However, the role played by the intrinsic properties of

the TSS wavefunction in defining the highest spin polarization that could be achieved, for instance in d.c. and photoinduced electrical currents, has remained elusive.

We report here that the TSS many-layer-deep extension into the material’s bulk – in concert with strong SOI – gives rise to a layer-dependent, entangled spin-orbital texture of the Dirac fermions in Bi_2Se_3 . This enables the precise control of both in- and out-of-plane spin polarization of the photocurrent in spin-resolved ARPES – all the way from 0 to $\pm 100\%$ – by varying energy, polarization, and angle of incidence of the incoming photons. More generally, the layer-by-layer variation in spin-orbital entanglement is of fundamental importance to spintronic studies and applications, whose outcome will depend critically on how one couples to the TSS. A remarkable consequence, which we will specifically exploit in this study, is that one can gain exquisite sensitivity to the internal structure of the TSS wavefunction, Ψ_{TSS} , via quantum interference effects using ARPES. In particular, the spin-orbital texture is captured directly in the linear-polarization dependence of the ARPES intensity maps in momentum space, and can be fully resolved with the aid of ab-initio DFT slab-calculations.

Let us start our discussion from the Bi_2Se_3 ARPES results in Fig. 1, measured with σ and π linearly-polarized 21.2 eV photons [22]. Based on our experimental geometry (Fig. 1A) and the photoemission selection rules, σ -polarized light probes mainly the in-plane p_x and p_y orbitals, whereas π -polarized light a combination of both in-plane and out-of plane (p_z) orbitals: the observed 80% reduction in overall intensity by switching from π - to σ -polarization indicates that the TSS has a dominant p_z orbital character. As for the evolution of the ARPES in-

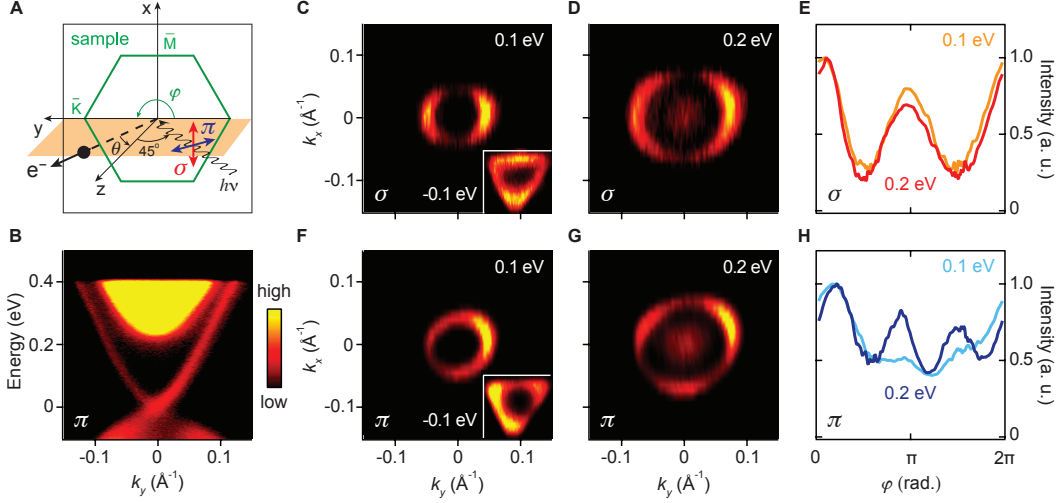


Fig. 1. **Linear polarization dependence of the measured ARPES intensity in momentum space.** (A) Schematics of the experimental geometry, with π (horizontal) and σ (vertical) linear polarizations, and horizontal photoelectron emission plane. (B) ARPES dispersion measured along $\bar{K}$ – Γ – $\bar{K}$ with π polarization; the zero of energy – here and throughout the paper – has been set at the Dirac point (DP) for convenience. (C–D) Constant energy ARPES maps from above (0.1 and 0.2 eV) and below (–0.1 eV, inset) the DP, measured with σ polarization; (F–G) same for π polarization. (E, H) Normalized variation of the σ - (E) and π -polarization (H) ARPES intensity, along the Dirac contours, plotted as a function of the in-plane angle φ .

tensity around the Dirac cone, in σ -polarization (Fig. 1C and E) we observe a twofold pattern at both 0.1 and 0.2 eV binding energy above the Dirac point (DP), consistent with a previous report [23], although somewhat asymmetric with respect to the $k_y = 0$ plane (see in particular Fig. 1E); this suggests a tangential alignment of the in-plane $p_{x,y}$ orbitals with respect to the Dirac constant-energy contours. Conversely in π -polarization (Fig. 1F–H) we observe an unprecedented onefold, strongly asymmetric pattern at 0.1 eV above the DP, which evolves into a threefold pattern while still retaining some asymmetry at 0.2 eV; this is in stark contrast with the uniform distribution of intensity along the Dirac contour expected for the dominant p_z orbitals. Finally, at –0.1 eV below the DP, a threefold pattern is observed for both polarizations (inset in C and F).

The asymmetry in ARPES intensity between $\pm \mathbf{k}_{\parallel}$ is particularly evident in π -polarization at 0.1 eV in Fig. 1F and in the band dispersion of Fig. 1B. This finding, which might seem in conflict with the time-reversal invariance of the TSS, provides fundamental clues on the structure of Ψ_{TSS} . Time-reversal invariance requires the state at $+\mathbf{k}$ with (pseudo) spin up to be degenerate with the state at $-\mathbf{k}$ with (pseudo) spin down, i.e. to have the same real-orbital occupation numbers. This so-called Kramers degeneracy, together with the ARPES selection rules for linearly polarized light, forbids intensity patterns which are different at $\pm \mathbf{k}$. We emphasize here that this restriction can be rephrased in terms of purely in-plane momentum coordinates, i.e. $\pm \mathbf{k}_{\parallel}$, only for a perfect 2-dimensional TSS with a delta-function-like density, for which k_z plays no role. Thus the observation of an imbal-

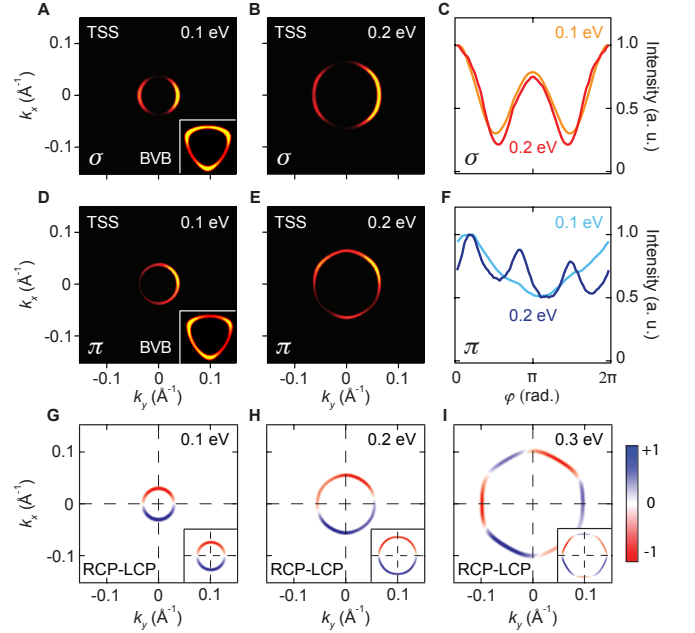


Fig. 2. **Calculated ARPES polarization dependence.** (A, B) Constant energy maps of the σ -polarization ARPES intensity from the topological surface state (TSS, 0.1 and 0.2 eV [24]) and bulk valence band (BVB, –0.1 eV in the inset); (C) corresponding variation of the ARPES intensity as a function of the in-plane angle φ . (D–F) Same data as in (A–C), but now for π -polarized light. (G–I) Calculated constant-energy ARPES patterns at 0.1, 0.2, and 0.3 eV above the DP; the insets show the patterns obtained by rotating the sample by 90° about the sample normal.

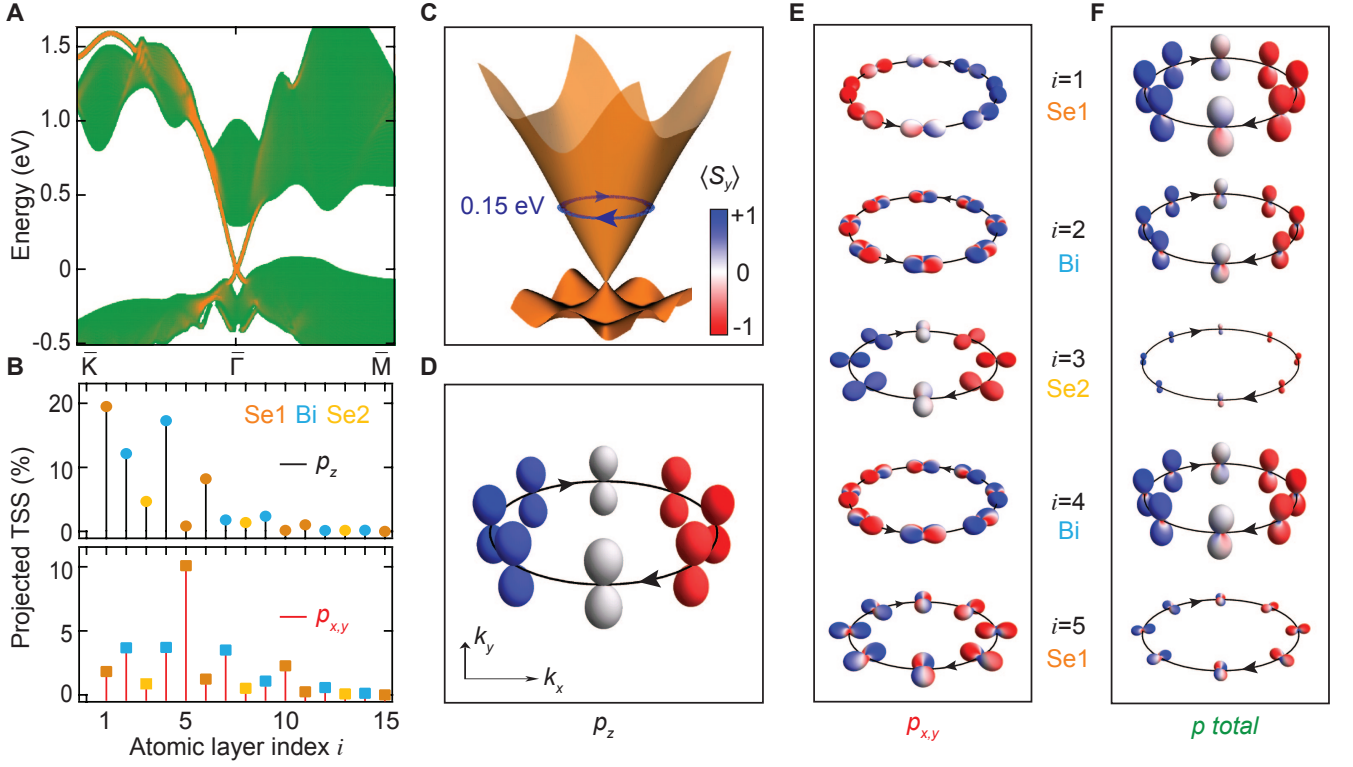


Fig. 3. **Layer-by-layer entangled spin-orbital texture of the TSS.** (A) Electronic dispersion from our 250-layer-slab DFT model [22], with TSS in orange and bulk states in green (Ψ_{TSS} is composed of those states that exceed a 20% projection onto the top 5 atomic layers in real space). (B) Percentage contribution of p_z and $p_{x,y}$ orbitals to Ψ_{TSS} at 0.15 eV above the DP, resolved layer-by-layer, for the top 15 atomic layers of the slab (Se1 is the natural cleavage plane). (D-F) Layer- and orbital-projected charge density along the 0.15 eV k -space contour indicated in (C): surfaces are defined by $r(\theta, \phi) = \sum_{\tau, \tau'} Z_{\tau}(\theta, \phi) Z_{\tau'}(\theta, \phi) \langle a_{i, \tau, k}^\dagger a_{i, \tau', k} \rangle$, where i and τ are the layer and local orbital basis indexes, and Z the cubic harmonics; the surface color represents the expectation value of the S_y operator. While the p_z channel is layer independent (D), a strong layer-dependent spin-orbital entanglement is observed for $p_{x,y}$ (E). The total layer-resolved TSS texture (F) is obtained by adding all p orbital contributions according to their relative, layer-dependent weight from panel (B).

ance in ARPES intensity at $\pm \mathbf{k}_{\parallel}$, together with the established time-reversal invariance of TIs, necessarily implies that Ψ_{TSS} must have a finite extent – albeit not a dispersion [25] – along the third dimension. While details will become clear when discussing our DFT results in Fig. 3, we anticipate that this – together with the strong SOI – leads to a complex layer-dependent spin-orbital entanglement in Bi_2Se_3 , which becomes apparent in ARPES through photoelectron interference effects.

Before delving into the analysis of the layer-resolved Ψ_{TSS} we note that, by performing ARPES intensity calculations [22, 26] for the extended TSS and bulk wavefunctions from our DFT slab-calculations, we accurately reproduce polarization-dependent ARPES experiments. As shown in Fig. 2A-F, we obtain very different intensities at $\pm \mathbf{k}_{\parallel}$ in excellent agreement with the results for both σ and π polarizations. Specifically, we reproduce the approximately twofold pattern in σ polarization, stemming from the spatial configuration of $p_{x,y}$ orbitals (Fig. 2A and B); and also the threefold pattern away from the DP (Fig. 2E and insets of A and D), which

originates from the hybridization between TSS and bulk states (and is associated with the k_z dispersion of the latter [27]). As a final test of the robustness of our DFT analysis of Ψ_{TSS} , we have calculated constant-energy circular dichroism ARPES patterns, which are also in excellent agreement with previous studies [28, 29].

To gain a microscopic understanding of the properties of Ψ_{TSS} we present our DFT results for a 250-layer slab of Bi_2Se_3 [22] in Fig. 3A, with bulk states in green and TSS in orange. The in- and out-of-plane p orbital projections in Fig. 3B confirm that Ψ_{TSS} indeed has a large p_z (70%) character, although $p_{x,y}$ (30%) is also significant, and most importantly that Ψ_{TSS} extends deep into the solid. Even though the orbital weight decays exponentially with the distance from the surface, as expected for a surface bound-state, Ψ_{TSS} extends approximately 2 quintupole layers (QL) below the surface (~ 2 nm), with $\sim 75\%$ contribution from the 1st QL and $\sim 25\%$ from the 2nd QL. Note also the interesting layer dependence of the orbital character: while for most layers the main component is the out-of-plane p_z , for the 5th (for example) the

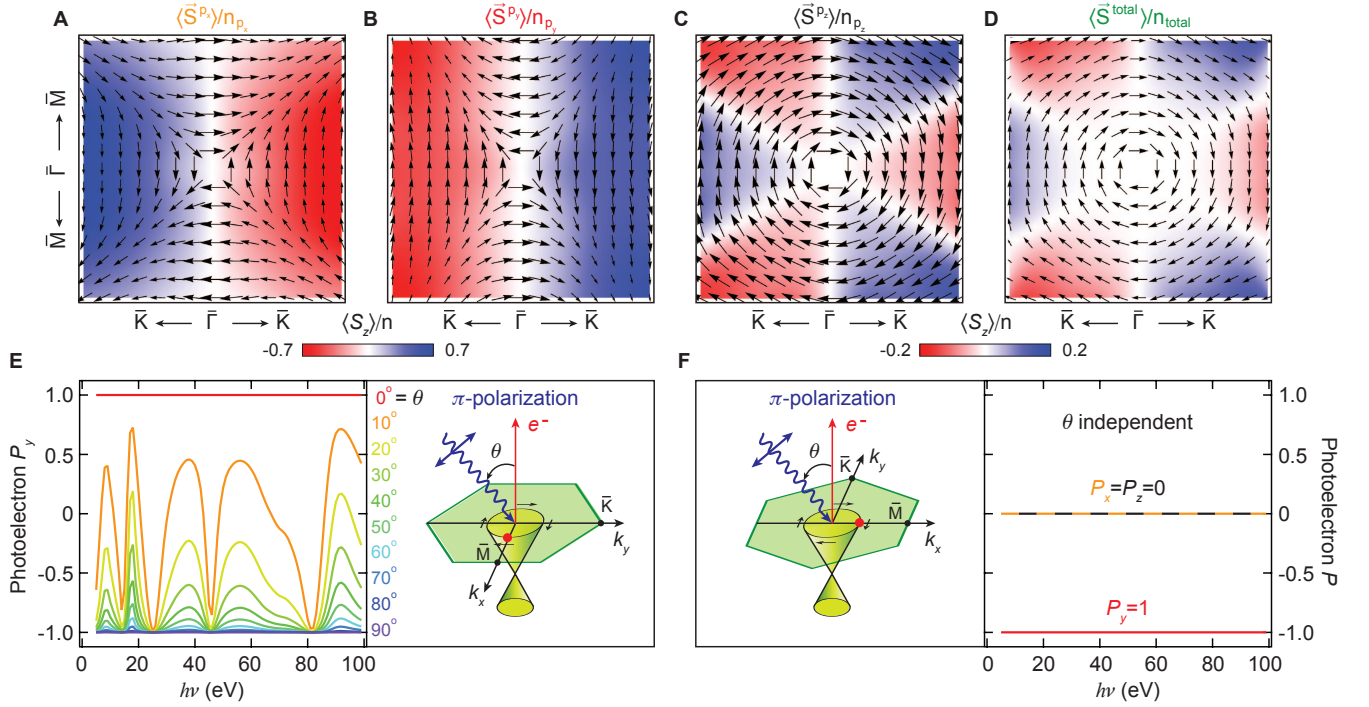


Fig. 4. **TSS spin texture and photoelectron spin polarization.** (A–D) Spin texture of the Dirac cone upper branch in Bi₂Se₃ obtained from the expectation value of the layer-integrated, orbital-projected spin operators, normalized to the orbital occupation [22]; in-plane and out-of-plane spin components are represented by arrows and colors, respectively. Note that (A–B) and (C–D) have different color scales but that the arrow scaling remains the same, with the largest arrows representing full polarization; also, moving away from $\bar{\Gamma}$ corresponds to moving along the Dirac dispersion away from the DP (~ 0.4 eV at maps edge). (E–F) Prediction for the photoelectron spin polarization (P) measured in spin-resolved ARPES as a function of photon energy and incidence angle [22]; two experimental geometries are examined in π polarization for the same k point located at 0.15 eV along $\bar{\Gamma}$ – $\bar{M}$, as indicated in the sketches [in (E) only the P component along y is shown].

in-plane $p_{x,y}$ is actually dominant.

As a consequence of the relativistic SOI, which directly connects orbital to spin flips via the $l^\pm s^\mp$ terms of the spin-orbit operator $\mathbf{l} \cdot \mathbf{s} = l_z s_z + (l^+ s^- + l^- s^+)/2$, the strongly layer-dependent orbital occupation becomes entangled with the spin polarization of Ψ_{TSS} . To visualize this entanglement, in Fig. 3D–F we present the layer- and orbital-projected charge density along the 0.15 eV Dirac contour indicated in Fig. 3C, with surface colors representing the expectation value of the S_y operator [22]. The p_z -projected charge density, being associated with a single orbital, cannot be entangled and has the layer-independent spin helicity shown in Fig. 3D [30]. In contrast, a strong layer-dependent spin-orbital entanglement is observed for $p_{x,y}$ because the eigenstates can be a linear combination of $p_{x,\uparrow}$, $p_{y,\downarrow}$, and similar states, resulting in a complex set of charge-density surfaces. These surfaces show two overall spatial configurations having opposite spin helicity, which are oriented tangentially and radially with respect to the Dirac cone contour [31], as seen in Fig. 3E. In Fig. 3F we show the total layer-dependent charge density obtained by adding in- and out-of-plane contributions according to their relative weights in Fig. 3B; from this it is clear that while the p_z orbitals

dominate, the in-plane $p_{x,y}$ orbitals lead to a substantial spin-orbital entanglement of the combined Ψ_{TSS} .

This entanglement also leads to complex in- and out-of-plane spin-texture, as shown in Fig. 4A–D where the layer-integrated spin patterns of individual and total p orbitals are presented. While for p_z we find the in-plane helical spin texture expected for the TSS this is not the case for the p_x and p_y orbitals, which exhibit patterns opposite to one another. Combining all contributions [$\langle \vec{S}^{\text{total}} \rangle / n_{\text{total}}$ in Fig. 4D], the TSS out-of-plane spin texture vanishes in the vicinity of the DP; most important, the in-plane spin polarization is reduced from 100% to 75% at the DP, and to 60% at 0.4 eV above the DP [22]. Note that this is also critically dependent on the relative $p_{x,y}$ orbital content of Ψ_{TSS} , which increases from 25% to 45% over the same energy range [22].

We will now highlight the interplay between the spin-orbital texture of Ψ_{TSS} , photoelectron interference, and the measured ARPES intensity. While a complete derivation – inclusive of selection rules, Bi and Se cross sections, as well as photoelectron escape depth – is given in the supporting online material [22], for the purpose of this discussion we approximate the ARPES intensity as $I \propto |\langle e^{i\mathbf{k} \cdot \mathbf{r}} | \mathbf{A} \cdot \mathbf{p} | \Psi_{\text{TSS}} \rangle|^2$, expressed in terms of plane-

wave photoelectron final states for simplicity. By writing Ψ_{TSS} as linear combination of the layer-dependent eigenstates, $\Psi_{\text{TSS}} = \sum_{i,\sigma} \alpha_i \psi_{i,\mathbf{k}_{\parallel}}^{\sigma}$ with i and σ being layer and spin indexes, the ARPES intensity then becomes $I \propto \sum_{\sigma} |\sum_i e^{-ik_z z_i} \langle e^{i\mathbf{k}_{\parallel} \cdot \mathbf{r}} | \mathbf{A} \cdot \mathbf{p} | \alpha_i \psi_{i,\mathbf{k}_{\parallel}}^{\sigma} \rangle|^2$. Here the $e^{-ik_z z_i}$ phase term accounts for the photoelectron optical path difference stemming from the TSS finite extent into the bulk. Because both $e^{-ik_z z_i}$ and $\psi_{i,\mathbf{k}_{\parallel}}^{\sigma}$ vary from layer to layer (the latter via the relative orbital content as shown in Fig. 3F), the photoemission intensity is dominated by interference between the $\psi_{i,\mathbf{k}_{\parallel}}^{\sigma}$ eigenstates, and can in fact be regarded as the Fourier transform of the layer-dependent Ψ_{TSS} . We also note that, because the phase of photoelectrons is defined by additive k_z and $\mathbf{k}_{\parallel}$ contributions, reversing the sign of either k_z or $\mathbf{k}_{\parallel}$ will change the ARPES intensity, i.e. $I(k_z) \neq I(-k_z)$ and especially $I(\mathbf{k}_{\parallel}) \neq I(-\mathbf{k}_{\parallel})$ as observed experimentally.

Photoelectron interference also severely affects the spin polarization $P_{x,y,z} = \frac{I^{\uparrow x,y,z} - I^{\downarrow x,y,z}}{I^{\uparrow x,y,z} + I^{\downarrow x,y,z}}$ measured in spin-resolved ARPES [22]. This exhibits a strong dependence on photon energy, polarization, and angle of incidence, which in general prevents the straightforward experimental determination of the intrinsic spin-texture of Bi_2Se_3 . While comprehensive results are presented in Fig. S2 and S3 [22], in Fig. 4E and F we show as an example the same k point along $\bar{\Gamma}-\bar{M}$ measured in two different geometries, probing selectively $p_{y,z}$ (E) and $p_{x,z}$ (F) orbitals. In Fig. 4E, because $\langle \vec{S}^y \rangle$ and $\langle \vec{S}^z \rangle$ (the spin polarization of the p_y and p_z orbitals) are antiparallel at this specific k point, P_y varies between $\pm 100\%$ upon changing θ , and oscillates wildly as a function of photon energy (with the exception of 0° and 90° , which probe p_y and p_z separately). However, if the sample is rotated by 90° as in Fig. 4F $\langle \vec{S}^x \rangle$ becomes parallel to $\langle \vec{S}^z \rangle$ and the measured $P_{x,y,z}$ are all independent of photon energy and incidence angle, allowing the detection of the intrinsic spin polarization. We note that this behavior is consistent with reported spin-resolved ARPES results [18]: for the situation of Fig. 4F, $P_y \gtrsim 80\%$ was obtained, close to our 100% expectation; along $\bar{\Gamma}-\bar{K}$, P_y was observed to vary from 25% at $h\nu = 36\text{ eV}$ to -50% at 70 eV , while we obtain $+20 \pm 10\%$ and $-40 \pm 15\%$, respectively [22].

In conclusion, we have shown that the spatial extent of the TSS into the solid and its strong layer-dependent spin-orbital entanglement are responsible – via photoelectron interference – for the apparent time-reversal symmetry breaking in ARPES and the large discrepancy in the estimated TSS spin-polarization from spin-resolved ARPES. This is of critical importance for many applications and fundamental studies of TIs. For instance we note that the photoelectron interference responsible for $I(\mathbf{k}_{\parallel}) \neq I(-\mathbf{k}_{\parallel})$ in ARPES also provides an explanation for the so-far puzzling observation of spin-polarized electrical currents photoinduced by linearly-polarized light [32], which also is associated with an im-

balance in the number of photoelectrons removed at $\pm \mathbf{k}_{\parallel}$. In addition, exploiting photoelectron interference in spin-resolved ARPES provides a way not only to probe the intrinsic spin texture of TIs, but also – and most importantly – to continuously manipulate the spin polarization of photoelectrons and photocurrents all the way from 0 to $\pm 100\%$ by an appropriate choice of photon energy, polarization, and angle of incidence.

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- [30] Note that in the k_y direction the charge density is white because a state with spin in the x direction is written as a linear combination of states with equal amount of spin *up* and spin *down* along the y direction.
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Additional information

Supporting online material is available in the online version of the paper. Correspondence and requests for materials should be addressed to A.D.